Diamagnetic excitons and exciton magnetopolaritons in semiconductors

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Influence of strained drain on performance of ballistic channel devices
Abudareheman Abdukelimu, Wufier Yaseunjang, Kunyuki Kakushima, Panth Ahmet, Mamtimin Geni, Kenji Natori and Hiroshi Iwai

Performance modeling of MWIR InAs/GaSb/InAlGaAs–InGaSb type-II superlattice nBn detector
P Martynuk, J Wrobel, E Pluc, P Madejczyk, A Kowalewski, W Gawron, S Krishna and A Rogałski

Optical loss in bent-waveguide superluminescent diodes
Qi An, Peng Jin, Ju Wu and Zhanqiu Wang

First polarization-engineered compressively strained AlInGaN barrier enhancement-mode MISFET
Herwig Hahn, Ben Reuters, Ada Wille, Nico Kettensiss, Fouad Benkhelifa, Oliver Ambacher, Holger Kalisch and Andrei Vescan

Fully implanted vertical p-i-n diodes using high-purity semi-insulating 4H-SIC wafers
R Ngoc, A Naht, F Moxiaetelli, P Da Nicola, Y-L Tian and M V Rao

Dispersive spectra and Fröhlich electron–phonon interaction Hamiltonians of full polar optical phonon states in a wurtzite nitride nanowire: quantum size effect
L Zhang and J J Shi

Characteristics of surface mount low barrier silicon Schottky diodes with boron contamination in the substrate-epitaxial layer interface
Debdas Pal, David Hoog and Margaret Barter

Light-dependent I-V characteristics of TiO\textsubscript{2}/CdTe heterojunction solar cells
V V Brus, M I Ilashchuk, Z D Kovalyuk and P D Maryanchuk

Properties and fabrication of high-order Bragg gratings for wavelength stabilization of diode lasers

Tunable surface plasmon polaritons in metal-strip waveguides with magnetized semiconductor substrates in Voigt configuration
Gishamol Mathew and Vincent Mathew

13 \textmu m diode lasers grown on (Al)GaInN/GaAs compositionally graded metamorphic buffer layers
T Hosoda, D Wang, G Kipshidze, W L Sarney, L Sherevets and G Belenky

Polarization-reduced quaternary InAlGaN/GaN HFET and MISFET devices
N Kettensiss, A Askar, B Reuters, A Noceulak, B Hollander, H Kalisch and A Vescan

Temperature-dependent efficiency droop in InGaN-based light-emitting diodes induced by current crowding
Ya Ya Kudryk, A K Tkachenko and A V Zinovchuk

Recombination and temperature distribution in semiconductors
Igor Lashkevych, Oleg Tiarov and Yuri Gurevich

Interface states in polymer thin-film transistors based on poly(3-hexylthiophene)
Yurong Liu, P T Lai, Ruobe Yao and Linfeng Deng

Spin phenomena in asymmetrical \{0 0 1\} GaN/Al\textsubscript{x}Ga\textsubscript{1-x} As quantum wells
P Trontz
Corrigendum: Growth and properties of III–V compound semiconductor heterostructure nanowires
Q Guo, H H Tan, H E Jackson, L M Smith, J M Yarrison-Rice, Jin Zou and C Jagadish

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